## NSN 5962-01-420-4650



Memory Microcircuit - Page 1 of 2 View Online at https://aerobasegroup.com/nsn/5962-01-420-4650 **Body Length:** 0.358 inches **Body Width:** 0.358 inches **Body Height:** 0.100 inches **Maximum Power Dissipation Rating:** 500.0 milliwatts **Operating Tempurature Range:** -55.0/+125.0 degrees celsius Storage Tempurature Range: -65.0/+150.0 degrees celsius **End Application:** Pacer dawn **Features Provided:** Burn in and electrostatic sensitive and hermetically sealed and programmed and positive outputs and monolithic **Inclosure Material:** Ceramic and glass **Inclosure Configuration:** Leadless flat pack **Output Logic Form:** Transistor-transistor logic **Input Circuit Pattern:** 10 input **Criticality Code Justification:** Cbbl **Case Outline Source And Designator:** C-2 mil-m-38510 **Terminal Surface Treatment:** Solder **Product Name:** Microcircuit, programmed (pal 16r8a-2) Voltage Rating And Type Per Characteristic: 7.0 volts power source **Time Rating Per Chacteristic:** 

25.00 nanoseconds propagation delay time, high to low level output and 25.00 nanoseconds propagation delay time, low to high level output

**Memory Device Type:** 

Pal

**Special Features:** 

Altered item, made from device p/n 81036122x, cage 67268, microcircuit, memory, programmable logic, monolithic silicon

**Test Data Document:** 

96906-mil-std883 standard (includes industry or association standards, individual manufactureer standards, etc.).

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Termi	inal	Type	And	Quantity:
20 lea	dles	ss		

Shelf Life:

N/a

**Unit Of Measure:** 

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Demilitarization:

No

Fiig:

A458a0